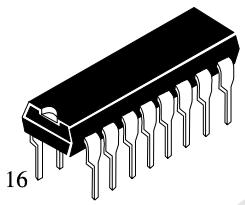
HIGH-VOLTAGE HIGH-CURRENT DARLINGTON TRANSISTOR ARRAYS

ILN2003A

The ILN2003A are monolithic high-voltage, high-current Darlington transistor arrays. Each consists of seven n-p-n Darlington pairs that feature high-voltage outputs with common-cathode clamp diodes for switching inductive loads. The collector-current rating of a single Darlington pair is 500 mA. The Darlington pairs may be paralleled for higher current capability. Applications include relay drivers, hammer drivers, lamp drivers, display drivers (LED and gas discharge), line drivers, and logic buffers.

The ILN2003A has a 2.7-k . series base resistor for each Darlington pair for operation directly with TTL or 5-V CMOS devices.

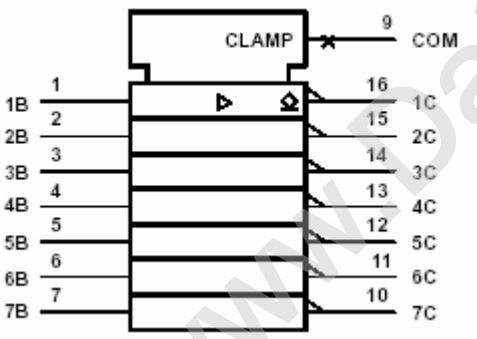


ORDERING INFORMATION

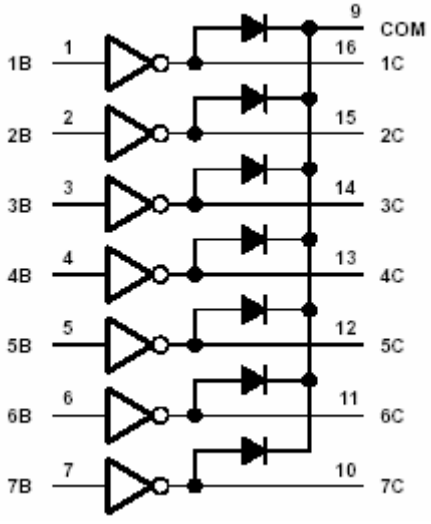
ILN2003AN Plastic
ILN2003AD SOIC
T_A = -20°C to 85° C for all packages

- 500-mA Rated Collector Current (Single Output)
- High-Voltage Outputs . . . 50 V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay Driver Applications

LOGIC SYSBOL



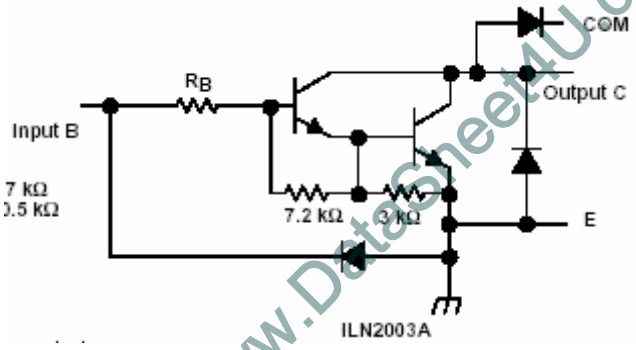
LOGIC DIAGRAM



SCHEMATICS (each Darlington Pair)

All resistor values shown are nominal.

ILN2003A: R_B = 2.7 kW



Absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Collector-emitter voltage	50 V
Input voltage, V_I (see Note 1)	30 V Peak
collector current (see Figures 14 and 15)	500 mA
Output clamp current, I_{OK}	500 mA
Total emitter-terminal current	–2.5 A
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T_A	–20°C to 85°C
Storage temperature range, Tstg	–65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

NOTE 1: All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.

DISSIPATION RATING TABLE

PACKAGE	T_A = 25°C POWER RATING	DERATING FACTOR ABOVE T_A = 25°C	T_A = 85°C POWER RATING
D	950 mW	7.6 mW/°C	494 mW
N	1150 mW	9.2 mW/°C	598 mW

Electrical characteristics, TA = 25°C (unless otherwise noted)

PARAMETER		TEST FIGURE	TEST CONDITIONS		ILN2003A MIN	ILN2003A TYP	ILN2003A MAX	UNIT
$V_{I(on)}$	On-state input voltage	6	V_{CE} = 2 V	I_C = 125 mA				V
				I_C = 200 mA			2.4	
				I_C = 250 mA			2.7	
				I_C = 275 mA				
				I_C = 300 mA			3	
				I_C = 350 mA				
$V_{CE(sat)}$	Collector-emitter saturation voltage	5	I_I = 250 µA,	I_C = 100 mA		0.9	1.1	V
			I_I = 350 µA,	I_C = 200 mA		1	1.3	
			I_I = 500 µA,	I_C = 350 mA		1.2	1.6	
I_{CEX}	Collector cutoff current	1	V_{CE} = 50 V,	I_I = 0			50	µA
		2	V_{CE} = 50 V, T_A = 70°C	I_I = 0			100	
				V_I = 1 V				
V_F	Clamp forward voltage	8	I_F = 350 mA			1.7	2	V
$I_{I(off)}$	Off-state input current	3	V_{CE} = 50 V, T_A = 70°C	I_C = 500 µA,	50	65		µA
I_I	Input current	4	V_I = 3.85 V			0.93	1.35	mA
			V_I = 5 V					
			V_I = 12 V					
I_R	Clamp reverse current	7	V_R = 50 V				50	µA
			V_R = 50 V,	T_A = 70°C			100	
C_I	Input capacitance		V_I = 0,	f = 1 MHz		15	25	pF

switching characteristics, T_A = 25°C

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output	See Figure 9		0.25	1	µs
t_{PHL}	Propagation delay time, high-to-low-level output			0.25	1	µs
V_{OH}	High-level output voltage after switching	V_S = 50 V, I_O = 300 mA, See Figure 10	V_S–20			mV

PARAMETER MEASUREMENT INFORMATION

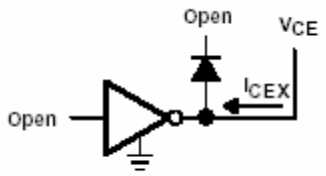


Figure 1. I_{CEX} Test Circuit

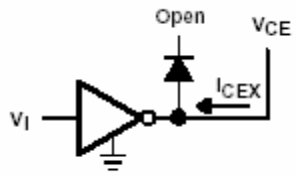


Figure 2. I_{CEX} Test Circuit

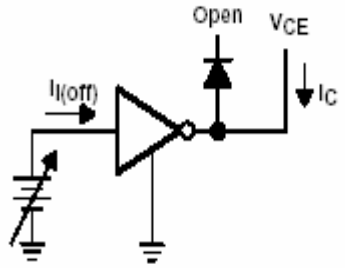


Figure 3. $I_{I(off)}$ Test Circuit

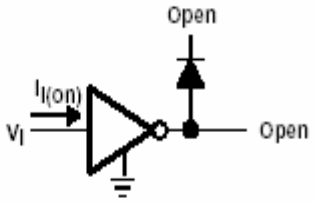
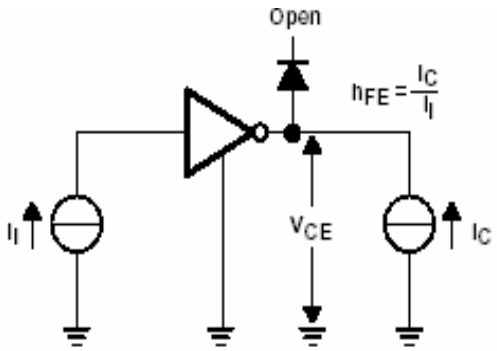


Figure 4. I_I Test Circuit



NOTE: I_I is fixed for measuring $V_{CE(sat)}$, variable for measuring h_{FE}.

Figure 5. h_{FE}, $V_{CE(sat)}$ Test Circuit

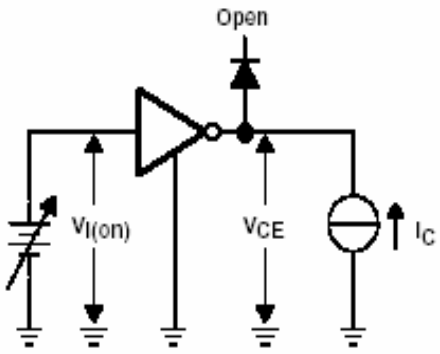


Figure 6. $V_{I(on)}$ Test Circuit

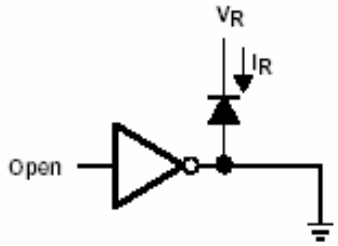


Figure 7. I_R Test Circuit

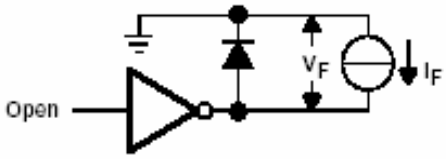


Figure 8. V_F Test Circuit

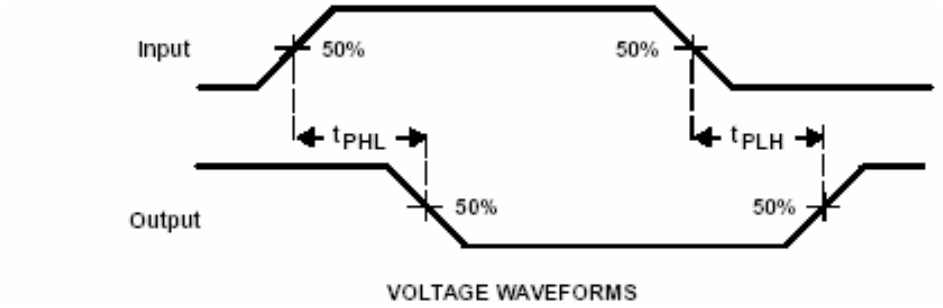
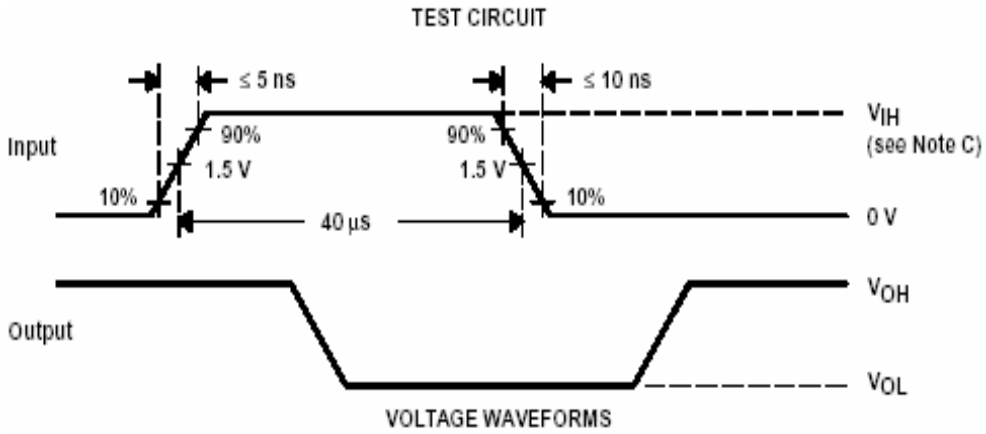


Figure 9. Propagation Delay-Time Waveforms



NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz, Z_O = 50 .
B. C_L includes probe and jig capacitance.
C. V_{IH} = 3 V;

Figure 10. Latch-Up Test Circuit and Voltage Waveforms

TYPICAL CHARACTERISTICS

COLLECTOR-EMITTER SATURATION VOLTAGE vs COLLECTOR CURRENT (ONE DARLINGTON)

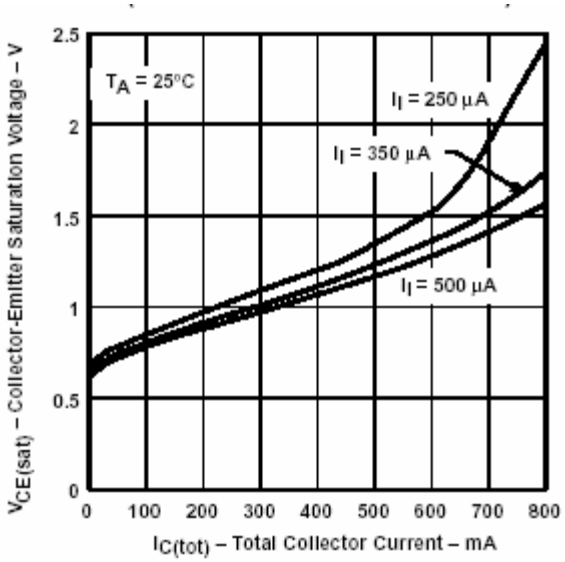


Figure 12

COLLECTOR-EMITTER SATURATION VOLTAGE vs TOTAL COLLECTOR CURRENT

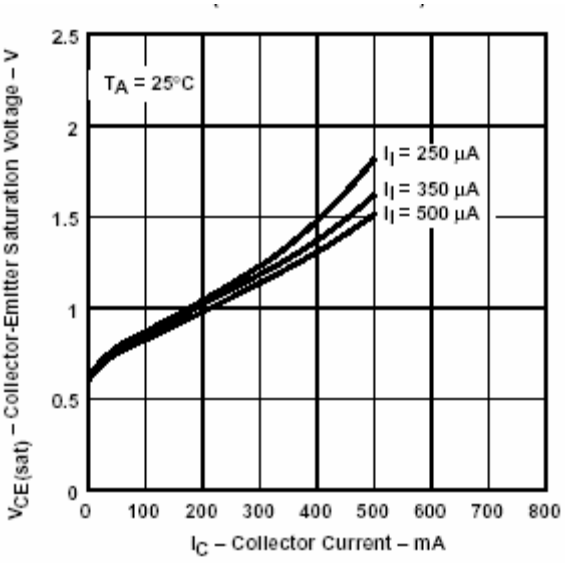


Figure 11

COLLECTOR CURRENT vs INPUT CURRENT

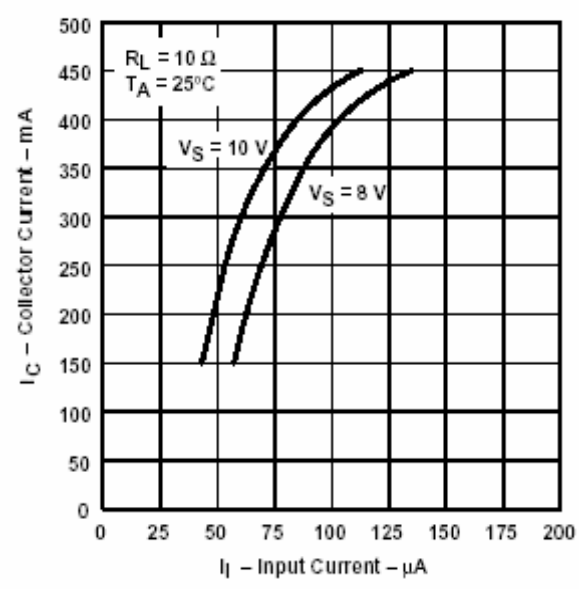


Figure 13

THERMAL INFORMATION

D PACKAGE
MAXIMUM COLLECTOR CURRENT
Vs
DUTY CYCLE

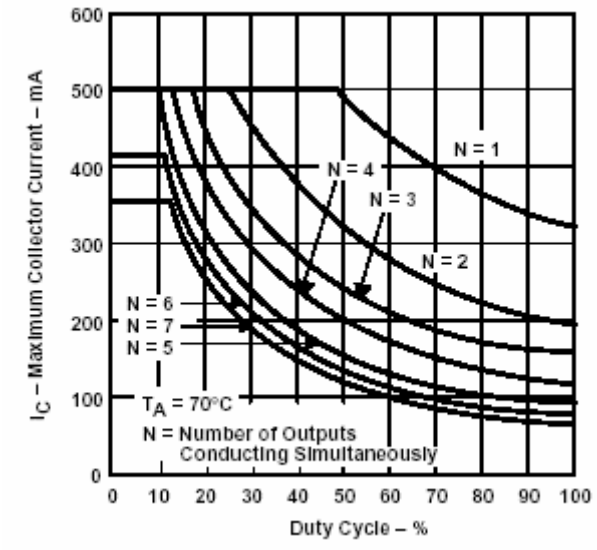


Figure 14

N PACKAGE
MAXIMUM COLLECTOR CURRENT
vs
DUTY CYCLE

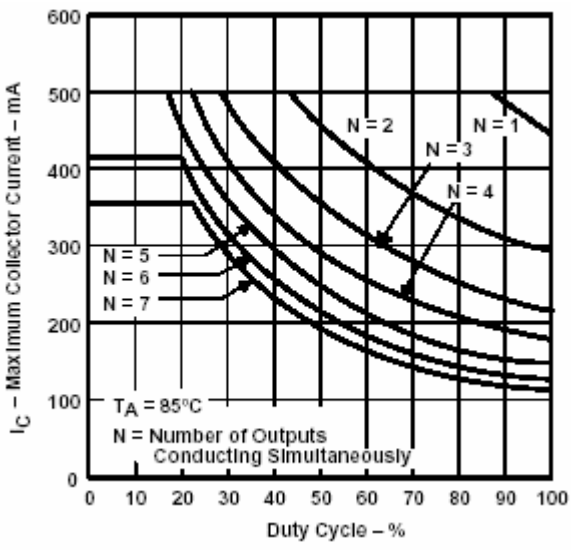


Figure 15

APPLICATION INFORMATION

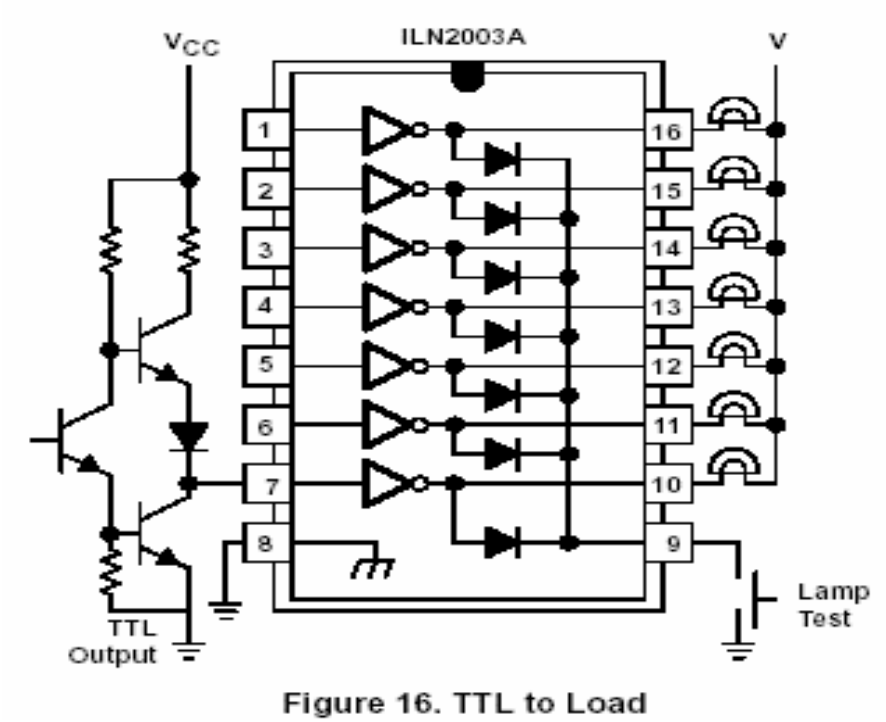


Figure 16. TTL to Load

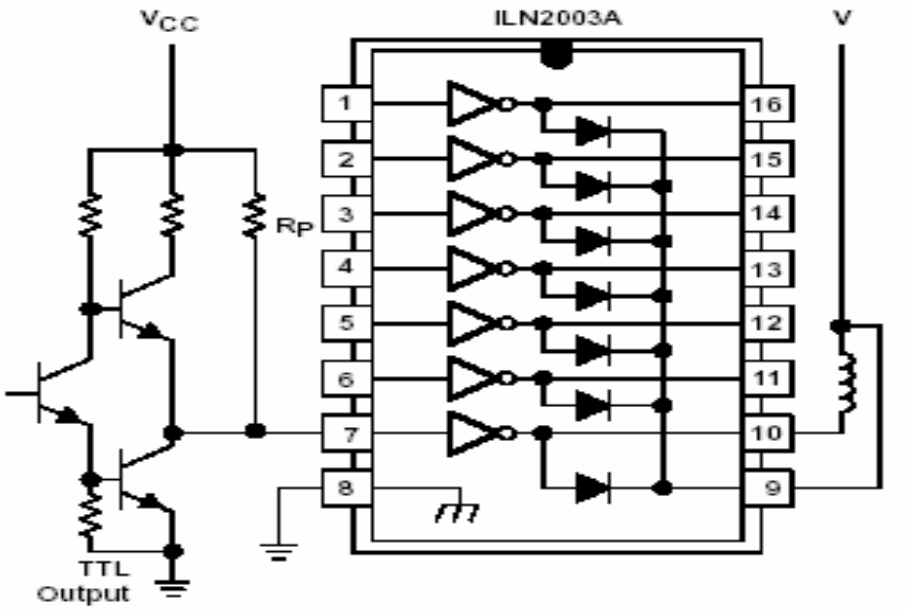
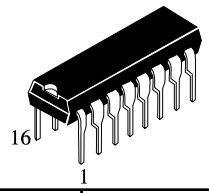
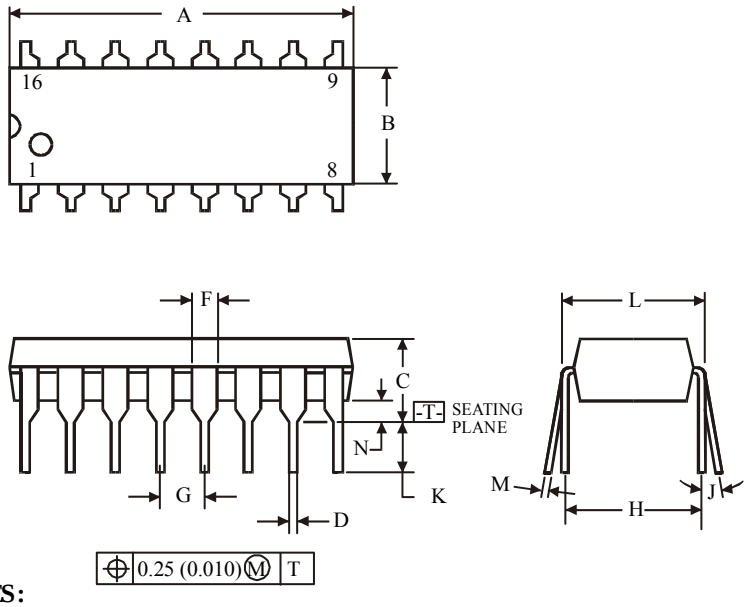


Figure 17. Use of Pullup Resistors to Increase Drive Current

N SUFFIX PLASTIC DIP
(MS - 001BB)



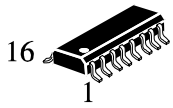


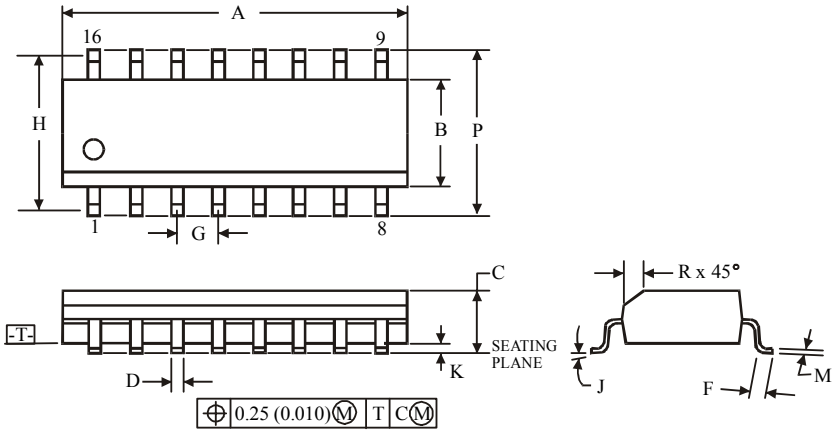
	Dimension, mm	
Symbol	**MIN**	**MAX**
A	18.67	19.69
B	6.10	7.11
C		5.33
D	0.36	0.56
F	1.14	1.78
G	2.54	
H	7.62	
J	0°	10°
K	2.92	3.81
L	7.62	8.26
M	0.20	0.36
N	0.38	

NOTES:

1. Dimensions “A”, “B” do not include mold flash or protrusions.
   Maximum mold flash or protrusions 0.25 mm (0.010) per side.

D SUFFIX SOIC
(MS - 012AC)





	Dimension, mm	
Symbol	**MIN**	**MAX**
A	9.80	10.00
B	3.80	4.00
C	1.35	1.75
D	0.33	0.51
F	0.40	1.27
G	1.27	
H	5.72	
J	0°	8°
K	0.10	0.25
M	0.19	0.25
P	5.80	6.20
R	0.25	0.50

NOTES:

1. Dimensions A and B do not include mold flash or protrusion.
2. Maximum mold flash or protrusion 0.15 mm (0.006) per side
   for A; for B – 0.25 mm (0.010) per side.